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ABSTRACT OF THE DISCLOSURE

The semiconductor device has a low-resistance layer provided under the interconnection extending from the signal input to a gate of MOSFET. The low-resistance layer ~~decreases~~ <sup>FEI</sup> ~~the substrate resistance~~ and the noise characteristic of the semiconductor device can also be improved. The low-resistance layer can be provided on a surface of the substrate or a polysilicon interconnection.

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